Crystallization processes are constantly being developed to match the rising industry needs such as better flow ability, compressibility and dissolution properties, to name a few, which in turn can be enhanced by crystal habit modification process where normally impurities are intentionally added during the crystallization process. Furthermore, crystal habit modification by impurity incorporation provides a good scenario to study fundamental aspects of the surface chemistry role in the crystal growth mechanism since even low levels of impurity can lead to substantial changes in the final morphology. Once incorporated, impurity can act either by blocking the movement of step/kink surface sites or disturbing the proper molecular packing of the next growing layer [1]. However, structural changes in crystal habit modification due to impurity incorporation still lacks investigations on lattice distortions that could bring new insights for both fundamental science and industrial crystallization process.

Sodium bromate (NaBrO3) grown under moderate supersaturation crystalizes in the space group P213 (a = 6.7072 Å) and presents a habit mainly ruled by the tetrahedral faces of the “positive” {111}-form (defined by {111}, {1-1-1}, {-11-1} and {-1-11} faces) with the presence of the less important “negative” tetrahedral {-1-1-1}-form (with {-1-1-1}, {-111}, {1-11} and {11-1} faces). These symmetric but non-equivalent faces have a polar behavior from the P213 group and so present distinct surface chemistry that will rule the impurity incorporation selectivity between such faces. In this work, large nearly perfect single crystals of NaBrO3 were grown with and without the presence of habit modifying sodium dithionate (Na2S2O6) impurities from 50 up to 2000 ppm in molar ratio. Changes in the final habit have been observed, with the {-1-1-1}-form prevailing over the {111}-form at levels of 500 ppm or higher. Sulphur incorporation has been confirmed by X-ray fluorescence on all doped samples. X-ray Powder Diffraction (XPD) has shown similar profiles between pure and doped samples and thus indicates that the dopant was well incorporated by the host lattice. However, surface microtopography revealed an increase of the roughness as well as the presence of growth steps hillocks as the dopant level goes higher, which in turn indicates the occurrence of dislocations lines during the crystal growth, not detected by XPD. Studies on S2O62---doped NaClO3 crystals supports an incorporation mechanism in which one SO3- group substitutes the ClO3- ion, whilst the other SO3- causes high disturbance in the upcoming layers and its growth rate. This assumption is going to be verified for the NaBrO3 system using X-ray Multiple Diffraction (XRMD) technique that has enough sensitivity to detect minor distortions along the crystal lattice. The (000)(002)(111) and (000)(002)(-1-1-1) Bragg-Surface Diffraction (BSD) [2] cases are able to probe the lattice along two orthogonal directions inside the same growth sector and hence, identify any anisotropic strain caused by the S2O62- ion. BSD ω:φ mappings (coupled scans along both incident (ω) and azimuthal (φ) angles) are also useful to evaluate the mosaicity level along the in-plane and out-of-plane directions whilst maintain the Dynamical Diffraction regime [3].


**Keywords:** Crystal Habit, Sodium Bromate, X-ray Multiple Diffraction